

CCP

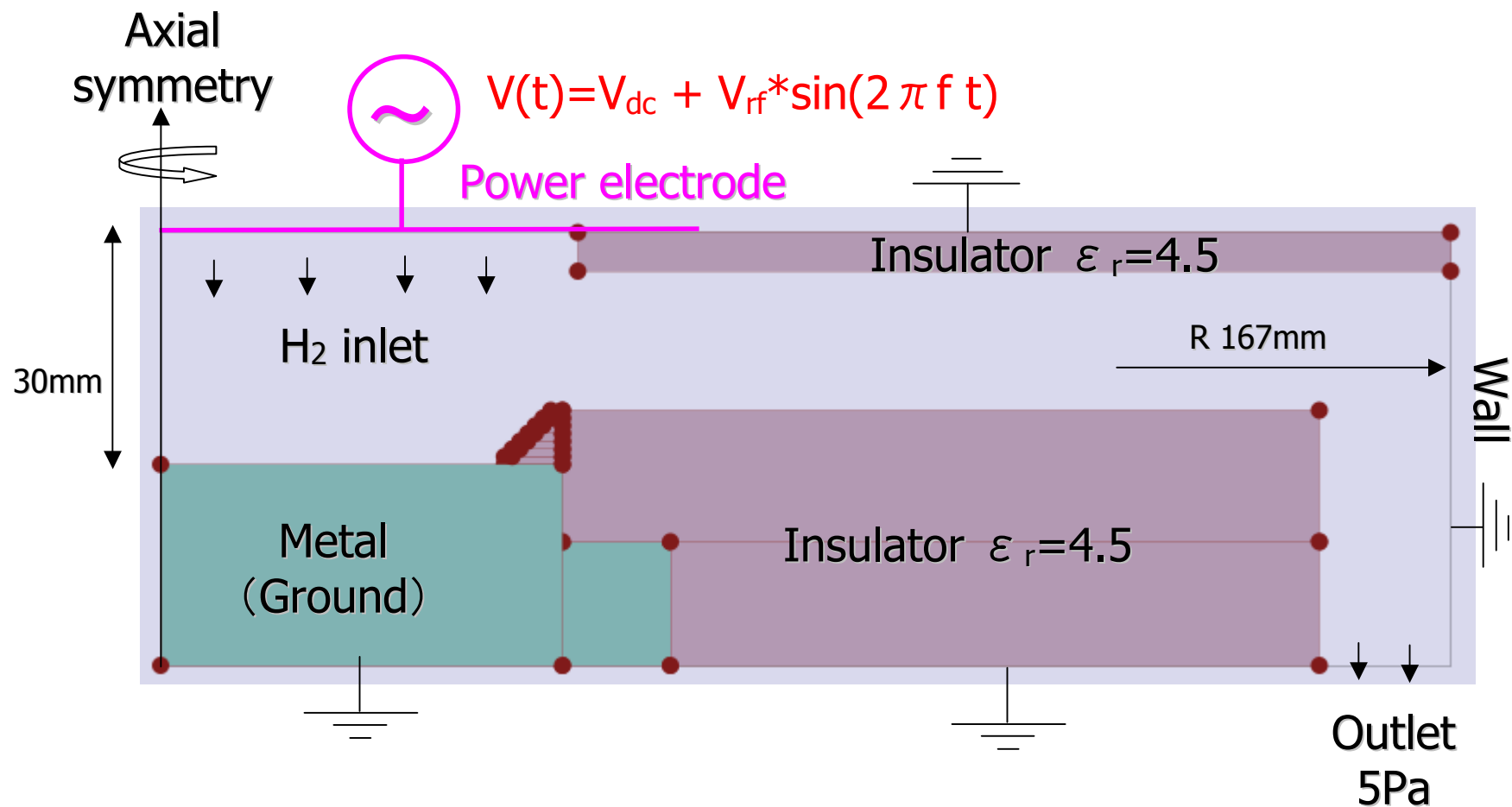
Hydrogen plasma simulation

**Modules : PIC-MCCM
NMEM**

Purpose

The simulation result and the measurement result in Prof. Hori Lab. of Nagoya University of the hydrogen plasma in a organic low-K etching reactor are compared.

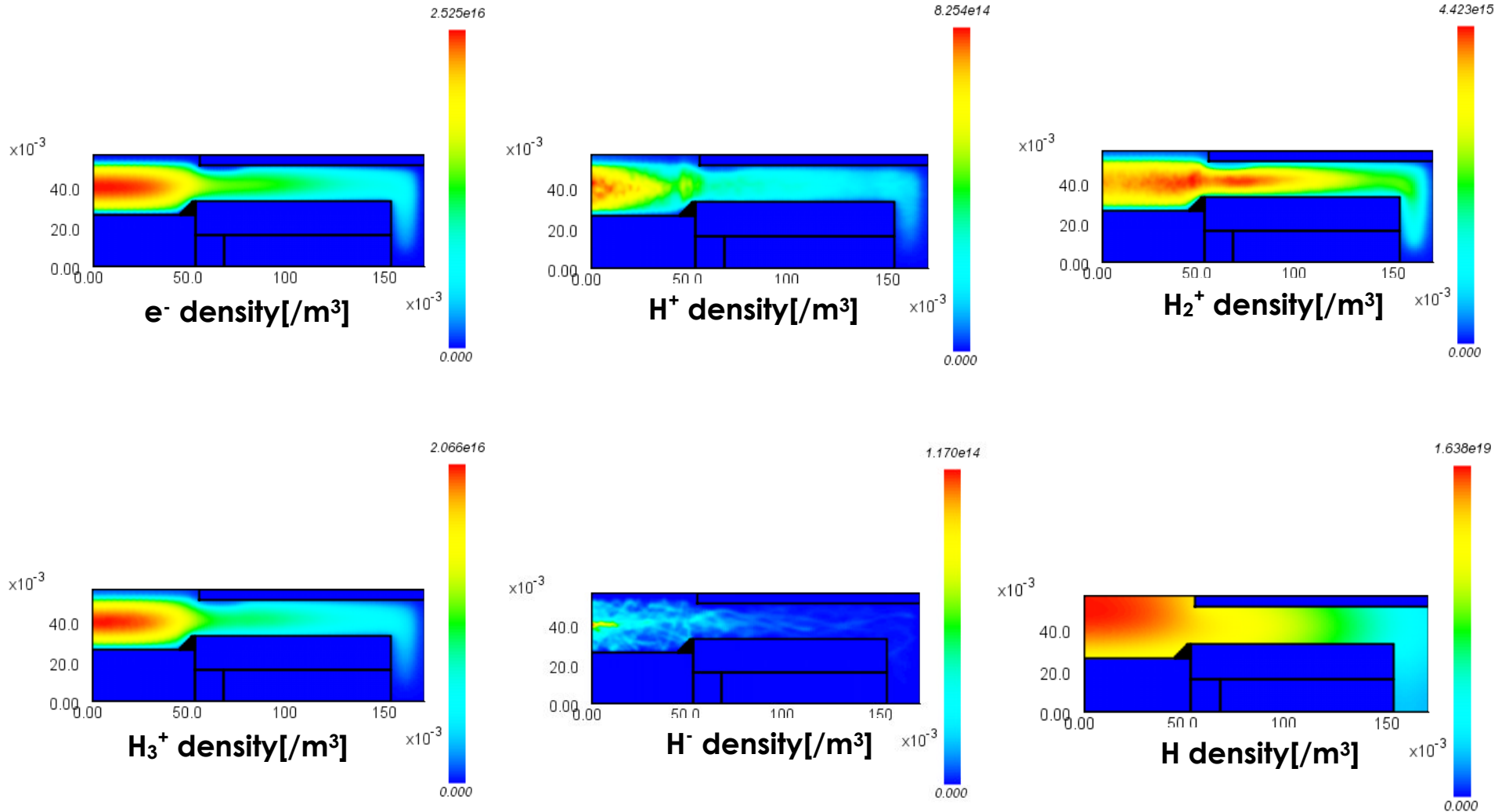
Computational model



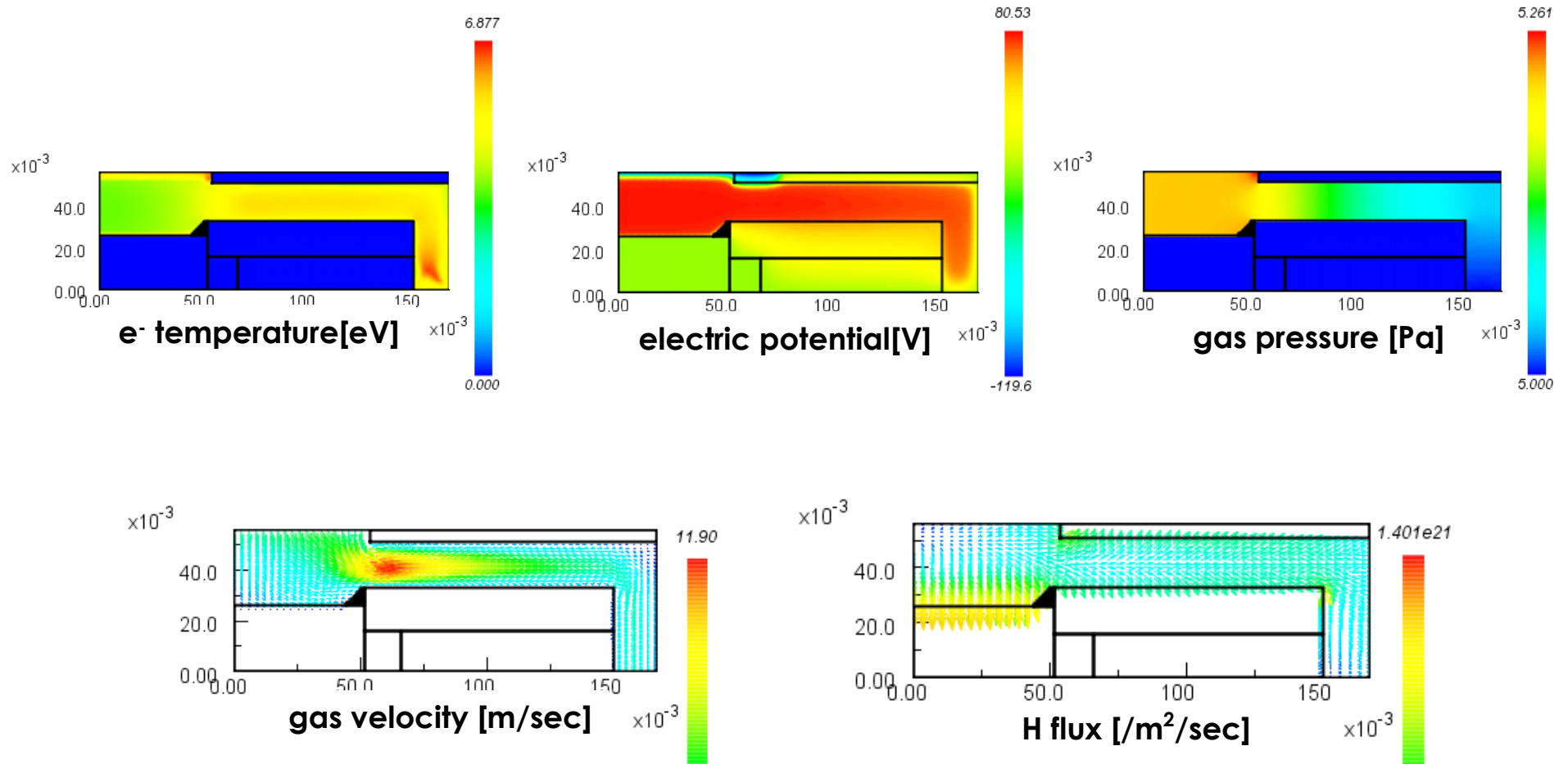
Computational conditions

- Pressure 5 [Pa] (Fixed at outlet)
- Power electrode $V_{rf}=200$ [V] ; frequency 60[MHz]
- V_{dc} : Automatically calculated
- Flow rate 200[sccm]
- Species to be considered
 $H_2, H, e^-, H^+, H_2^+, H_3^+, H^-$
- Reactions on the wall
 $H \rightarrow 1/2H_2$ (Metal surface 15% Insulator surface 7%)

Number density (electron, ions, Hydrogen atom)



Electron temperature, Electric potential, Gas pressure, Flow velocity, and H flux



Simulation result compared with experiment

quantity	Simulation(*)	experiment
Electron density [/cm ³]	1.44E10	1.6E10
H ⁺ density [/cm ³]	3.43E8	-
H ₂ ⁺ density [/cm ³]	3.45E9	-
H ₃ ⁺ density [/cm ³]	1.07E10	-
H ⁻ density [/cm ³]	1.29E7	-
H density [/cm ³]	1.13E13	2.0E13
Electron temperature [eV]	5.17	6.8
Vdc [V]	-112	-114

(*) These are mean values over radial direction at the center of electrodes.